# **Power MOSFET** 200 mA, 50 V

## N-Channel SOT-23

Typical applications are DC-DC converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

#### Features

- Low Threshold Voltage (V<sub>GS(th)</sub>: 0.5 V–1.5 V) Makes it Ideal for Low Voltage Applications
- Miniature SOT-23 Surface Mount Package Saves Board Space
- BVSS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

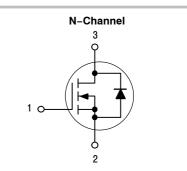


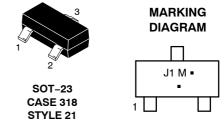
## **ON Semiconductor®**

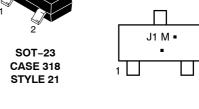
http://onsemi.com

200 mA, 50 V

 $R_{DS(on)} = 3.5 \Omega$ 







J1 = Device Code = Date Code\* Μ

= Pb-Free Package

(Note: Microdot may be in either location) \*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BSS138LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BVSS138LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BSS138LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise noted)

		-	
Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	50	Vdc
Gate-to-Source Voltage - Continuous	V <sub>GS</sub>	± 20	Vdc
Drain Current – Continuous @ $T_A = 25^{\circ}C$ – Pulsed Drain Current ( $t_p \le 10 \ \mu s$ )	I <sub>D</sub> I <sub>DM</sub>	200 800	mA
Total Power Dissipation @ $T_A = 25^{\circ}C$	PD	225	mW
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	– 55 to 150	°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	ΤL	260	°C

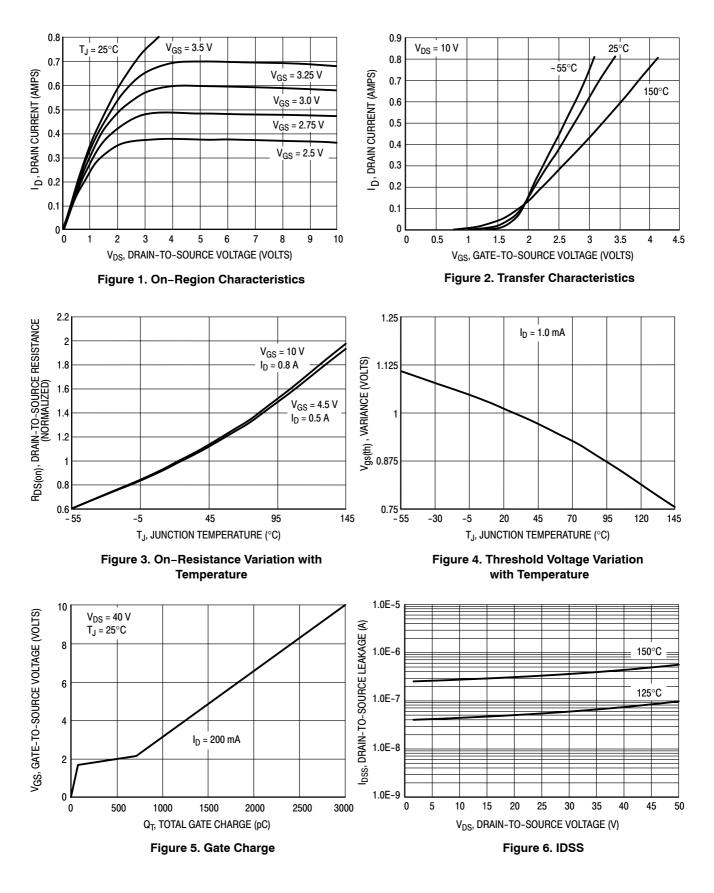
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS		•			•	
$\begin{array}{l} \mbox{Drain-to-Source Breakdown V} \\ \mbox{(V_{GS}=0 Vdc, I_{D}=250 \ \mu Adc} \end{array}$	V <sub>(BR)DSS</sub>	50	-	-	Vdc	
Zero Gate Voltage Drain Current $(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, 25^{\circ}\text{C})$ $(V_{DS} = 50 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, 25^{\circ}\text{C})$ $(V_{DS} = 50 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, 150^{\circ}\text{C})$					0.1 0.5 5.0	μAdc
Gate-Source Leakage Current	I <sub>GSS</sub>	-	-	±0.1	μAdc	
ON CHARACTERISTICS (Note	1)					
Gate-Source Threshold Voltag ( $V_{DS} = V_{GS}$ , $I_D = 1.0$ mAdc)	V <sub>GS(th)</sub>	0.5	-	1.5	Vdc	
Static Drain-to-Source On-Resistance (V <sub>GS</sub> = 2.75 Vdc, $I_D$ < 200 mAdc, $T_A$ = -40°C to +85°C) (V <sub>GS</sub> = 5.0 Vdc, $I_D$ = 200 mAdc)		r <sub>DS(on)</sub>		5.6 _	10 3.5	Ω
Forward Transconductance $(V_{DS} = 25 \text{ Vdc}, I_D = 200 \text{ mAc}$	9 <sub>fs</sub>	100	-	-	mmhos	
DYNAMIC CHARACTERISTICS						
Input Capacitance	$(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ MHz})$	C <sub>iss</sub>	-	40	50	pF
Output Capacitance	$(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ MHz})$	C <sub>oss</sub>	-	12	25	
Transfer Capacitance	$(V_{DG} = 25 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ MHz})$	C <sub>rss</sub>	-	3.5	5.0	
SWITCHING CHARACTERISTIC	CS (Note 2)	•	•	•	-	•
Turn-On Delay Time		t <sub>d(on)</sub>	-	-	20	ns
Turn-Off Delay Time	(V <sub>DD</sub> = 30 Vdc, I <sub>D</sub> = 0.2 Adc,)	t <sub>d(off)</sub>	-	_	20	

2. Switching characteristics are independent of operating junction temperature.

#### **TYPICAL ELECTRICAL CHARACTERISTICS**



#### **TYPICAL ELECTRICAL CHARACTERISTICS**

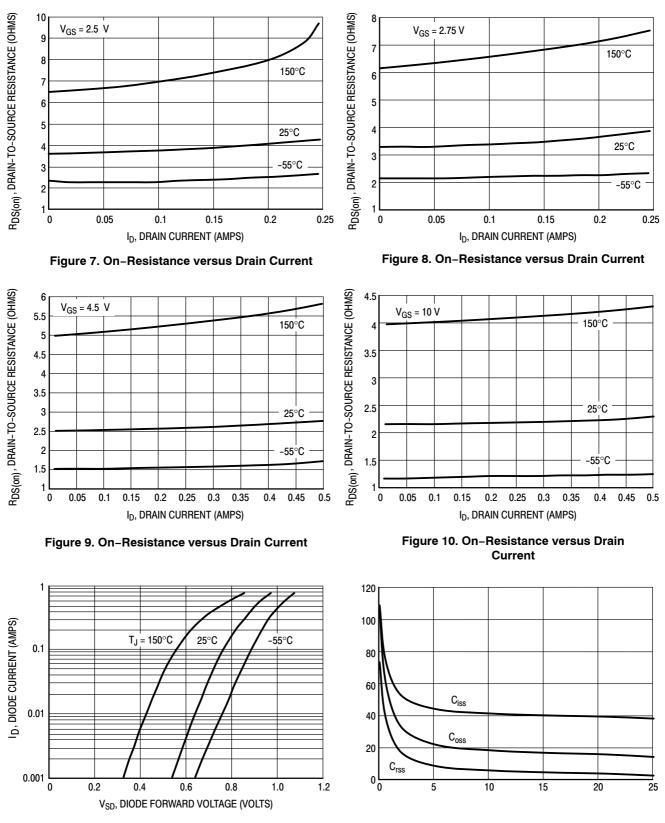
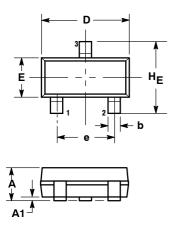


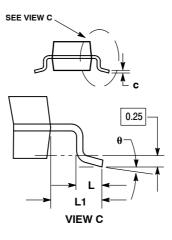
Figure 11. Body Diode Forward Voltage

Figure 12. Capacitance

#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP** 





NOTES

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 1. CONTROLLING DIMENSION: INCH. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH 2

3

THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

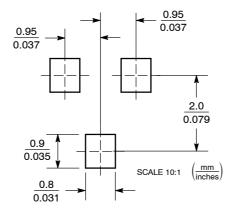
	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.040	0.044	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.018	0.020	
c	0.09	0.13	0.18	0.003	0.005	0.007	
D	2.80	2.90	3.04	0.110	0.114	0.120	
Е	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.081	
L	0.10	0.20	0.30	0.004	0.008	0.012	
L1	0.35	0.54	0.69	0.014	0.021	0.029	
HE	2.10	2.40	2.64	0.083	0.094	0.104	
θ	0°		10°	0°		10°	

STYLE 21: PIN 1. GATE

2. SOURCE

3. DRAIN

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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